Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H2682

APPLICATIONS

. Audio Power Amplifie.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature····· −55~150℃

T_j——Junction Temperature····· 150℃

P_C——Collector Dissipation（T_c=25℃）····· 8W

P_C——Collector Dissipation（T_A=25℃）····· 1.2W

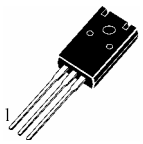
V_{CBO}——Collector-Base Voltage····· 180V

V_{CEO}——Collector-Emitter Voltage····· 180V

V_{EBO}——Emitter-Base Voltage····· 5V

I_C——Collector Current·····100mA

TO-126ML



1－Emitter，E
2－Collector，C
3－Base，B

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	180			V	I_C=100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	180			V	I_C=1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	I_E=10μA， I_C=0
I_{CBO}	Collector Cut-off Current			1	μA	V_{CB}=180V, I_E=0
I_{EBO}	Emitter Cut-off Current			1	μA	V_{EB}=3V, I_C=0
H_{FE}（1）	DC Current Gain	90	190			V_{CE}=5V, I_C=1mA
H_{FE}（2）	DC Current Gain	100		320		V_{CE}=5V, I_C=10mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.12	0.5	V	I_C=50mA, I_B=5mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		0.8	1.5	V	I_C=50mA, I_B=5mA
ft	Current Gain-Bandwidth Product		200		MHz	V_{CE}=10V, I_C=20mA,
Cob	Output Capacitance		3.2	5.0	pF	V_{CB}=10V, I_E=0,f=1MHz

h_{FE} Classification

O	Y
100—200	160—320